

L Number	Hits	Search Text	DB	Time stamp
-	31	(transistor and delay and library).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/30 11:29
-	1	transistor and curve and delay and region and segment\$3 and saturation adj region and linearity adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/30 16:39
-	46	transistor and curve and delay adj time and region and segment\$3 and saturation and linearity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/30 11:37
-	1	(transistor and delay adj time and segment\$3 and saturation adj region) and library	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/30 11:37
-	24	transistor and delay adj time and segment\$3 and saturation adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/30 13:32
-	132	delay adj time near3 simulat\$3 and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/30 13:33
-	51	(delay adj time near3 simulat\$3 and transistor) and MOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/30 14:54
-	13	(\$MOS and delay near3 estimat\$3).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/30 14:55
-	29961	"MOST" and delay adj time	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/30 16:39
-	22523	"MOST" and circuit and delay adj time	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/30 16:41
-	1	(MOS and model and circuit and delay adj time).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/30 16:41

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1	31	(transistor and delay and library).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 18:39
2	3	((transistor and delay and library).ab.) and (delay adj library)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 18:38
3	325	transistor and curve and delay adj time and region and segment\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 18:46
4	1	(transistor and curve and delay adj time and region and segment\$3) and (delay adj library)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 18:55
5	1	(transistor and curve and delay adj time and region and segment\$3) and (delay near3 library)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 18:54
6	1	(transistor and curve and delay adj time and region and segment\$3) and (delay near6 library)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 18:54
7	111	delay adj library	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 18:56
8	72	(delay adj library) and @ad<20001013	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 19:17
9	2	((delay adj library) and @ad<20001013) and (slew adj rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 19:17
-	31	(transistor and delay and library).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 18:37
-	1	transistor and curve and delay and region and segment\$3 and saturation adj region and linearity adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/30 16:39
-	46	transistor and curve and delay adj time and region and segment\$3 and saturation and linearity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 18:46

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	1	(transistor and delay adj time and segment\$3 and saturation adj region) and library	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/30 11:37
	24	transistor and delay adj time and segment\$3 and saturation adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/30 13:32
	132	delay adj time near3 simulat\$3 and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/30 13:33
	51	(delay adj time near3 simulat\$3 and transistor) and MOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/30 14:54
	13	(\$MOS and delay near3 estimat\$3).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/30 14:55
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	1	(MOS and model and circuit and delay adj time).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/30 16:41